Valence transition behavior of the doped Falicov-K im ballm odel at nonzero tem peratures

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A bstract

The extrapolation of small-cluster exact-diagonalization calculations is used to study the in wence of doping on valence transitions in the spinless Falicov-K imball model at nonzero temperatures. Two types of doping are examined, and namely, the substitution of rare-earth ions by non-magnetic ions that introduce (i) one or (ii) none additional electron (per non-magnetic ion) into the conduction band. It is found that the rst type of substitution increases the average f-state occupancy of rare-earth ions, whereas the second type of substitution has the opposite electron. The results obtained are used to describe valence transition behavior of samarium in the hexaboride solid solutions Sm $_1\ _{\rm x}$ M $_{\rm x}$ B $_6$ M = Y $^{3+}$; La $^{3+}$; S r $^{2+}$; Y b $^{2+}$) and a very good agreement of theoretical and experimental results is found.

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In the past decade, a considerable amount of e ort has been devoted to understanding of the multitude of anomalous physical properties of rare-earth and transition-metal compounds. Recent theoretical works based on exact numerical and analytical calculations showed that many of these anomalous features, e.g., m ixed valence phenomena, metal-insulator transitions, etc., can be described very well within dierent versions of the Falicov-Kimball model (FKM) [1, 2, 3]. In particular, it has been found that the spinless FKM, can describe the discontinuous valence and insulator-m etal transitions [4,5] (induced by external pressure) observed experim entally in som e rare-earth sul des, halides and borides [6]. A nice correspondence between theoretical and experim ental results has been found, for example, for Sm B₆ [5, 7, 8, 9], where the alternative explanation of form ation and disappearance of the energy gap in the electronic spectrum of SmB6 has been presented. For SmB6 a very good agreem ent of experim ental and theoretical results has been obtained also for nonzero tem peratures for both the tem perature dependence of the speci c heat as well as magnetic susceptibility [10]. In addition, it was found that the spinless FKM can describe the anomalous temperature increase of electrical conductivity in Sm B₆ (due to the valence transition) [11] as well as the low temperature behavior (due to the appearance of the in-gap structure) in this material [9, 12]. Recently, the FKM has been successfully used to describe the inelastic light scattering in the SmB₆ systems [13]. These results indicate that the spinless FKM is a quite good m icroscopic m odel that can describe, at least qualitatively, m any of anom alous features of rare-earth compounds. From this point of view it seems to be interesting to ask if this simple model can describe also another kind of experiments performed often in these materials, and namely, the in uence of doping on the valence transition behavior of system s. For Sm B 6 it has been found, for example [14, 15], that the substitution of Sm by non-magnetic divalent ions (e.g., Sr^{2+} ; Yb^{2+}) increases the average sam arium valence (the average occupancy of f orbitals decreases), whereas the substitution of Sm by non-magnetic trivalent ions (e.g., Y 3+; La3+) produces the opposite e ect. In this paper we try to describe the in uence of both types of substitutions on the average sam arium valence within the spinless FKM.

The spinless FKM is based on the coexistence of two dierent types of electronic states in given materials: localized, highly correlated ioniclike states and extended,

uncorrelated, B loch-like states. It is generally accepted that valence and insulatorm etal transitions result from a change in the occupation numbers of these electronic states, which remain them selves basically unchanged in their character. The Ham iltonian of the model can be written as the sum of three terms:

$$H = \sum_{ij}^{X} t_{ij} d_i^{\dagger} d_j + U \sum_{i}^{X} f_i^{\dagger} f_i d_i^{\dagger} d_i + E_f \sum_{i}^{X} f_i^{\dagger} f_i;$$
 (1)

where f_i^+ , f_i are the creation and annihilation operators for an electron in the localized f state of a rare-earth atom at lattice site i with binding energy E_f and d_i^+ , d_i are the creation and annihilation operators of the itinerant spinless electrons in the d-band W annier state at site i. The rst term of (1) is the kinetic energy corresponding to quantum-mechanical hopping of the itinerant d electrons between sites i and j. These intersite hopping transitions are described by the matrix elements t_{ij} , which are t if i and j are the nearest neighbors and zero otherwise (in the following all parameters are measured in units of t). The second term represents the on-site C oulomb interaction between the d-band electrons (with the total number $N_d = \frac{P}{i} d_i^+ d_i$) and the localized f electrons (with the total number $N_f = \frac{P}{i} f_i^+ f_i$). The third term stands for the localized f electrons whose sharp energy level is E_f . The Ham iltonian of the FKM doped by divalent (e.g., $S r^{2+}$) or trivalent (e.g., Y^{3+}) ions has the same form. From the numerical point of view there is only one dierence, and namely, the summation over all lattice sites (in the second and third term) should be replaced by summation over the sam arium positions.

Since in the spinless version of the FKM without hybridization the f-electron occupation number $f_i^+ f_i$ of each site i commutes with the Hamiltonian (1), the f-electron occupation number is a good quantum number, taking only two values: $w_i = 1$ or 0, according to whether or not the site i is occupied by the localized f electron. Then the Hamiltonian (1) can be written as

$$H = {}^{X} h_{ij} d_{i}^{+} d_{j} + E_{f} {}^{X} w_{i};$$
 (2)

where h_{ij} (w) = t_{ij} + U w $_{i}$ $_{ij}$.

Thus for a given f-electron con guration $w = fw_1; w_2 ::: w_L g$ de ned on the one or two-dimensional lattice of L sites with periodic boundary conditions, the

Ham iltonian (2) is the second-quantized version of the single-particle Ham iltonian h(w) = T + UW, where T is an L-square matrix with elements t_{ij} and W is the diagonal matrix with elements w_i . The behavior of this model at nonzero temperatures is studied using small-cluster exact-diagonalization calculations. In order to compensate partially for the small size of clusters, thermal properties of the system are investigated via the grand canonical ensemble.

The grand canonical partition function of the FKM [16] can be expressed directly in terms of the eigenvalues $_{i}$ of the single-particle operator h, which depend on the f-electron conguration specified by $w = fw_{i}g$, i.e.,

$$= {}^{X} e^{(E_{f})N_{f}} = {}^{Y^{L}} [1 + e^{(i_{j})}] :$$
(3)

The tem perature dependences (= $k_B T$) of the therm odynam ic quantities are calculated from this expression by using the standard statisticalm echanics procedure. For example, the total number of f-electrons N $_f$ and the internal energy (E) as functions of them ical potential are given by [17]

$$N_{f}() = \frac{0}{0E_{f}} \ln ;$$
 (4)

$$E() = \frac{1}{L}(\frac{0}{0} + \frac{0}{0}) \ln ;$$
 (5)

where = 1 = .

In the next, we consider (i) the substitution of rare-earth ions (e.g., Sm) by non-magnetic trivalent ions (e.g., Y $^{3+}$) which introduce conduction electrons into the d-conduction band (one electron per dopant) and (ii) the substitution of rare-earth ions by non-magnetic divalent ions (e.g., S $^{2+}$) which play a dilution role and reduce the number of conduction electrons in the d-conduction band (no additional electrons are introduced to the system). In the rst case the total number of electrons $N = N_f + N_d$ is equal to the total number of lattice sites L (the case of one electron per rare-earth atom is considered) while in the second case N = L - X, where X is the total number of dopants. Thus the rst step of numerical calculations is to determ ine the chemical potential corresponding to N = L and N = L - X, respectively. A flerwards n_f ; E and other them odynamic quantities can be calculated

num erically.

It should be noted that the sum mation over all f electron distributions in (3) should be replaced for the doped FKM by sum mation over all possible f-electron and dopant distributions, thereby strongly limiting numerical computations. Although the number of congurations can be reduced considerably by the use of symmetries of H, there is still a limit (L 20) on the size of clusters that can be studied with this method. However, we will show later that due to small sensitivity of the thermodynamic quantities of the FKM on L, already such small clusters can describe the thermodynamics of the model very well.

To describe e ects of doping by divalent and trivalent ions on the average f-state occupancy of rare-earth ions we have perform ed an exhaustive study of the model for a wide range of model parameters U; ;E $_{\rm f}$. The typical dependences of the average f-orbital occupancy $n_{\rm f}=N_{\rm f}=(L-X)$ on the dopant concentration x=X=L are displayed in Fig. 1 for E $_{\rm f}=0$; U=0.5 and several di-erent temperatures .

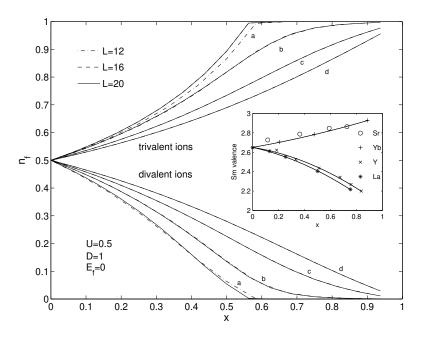


Figure 1: The average occupancy of f orbitals as a function of x for doping by divalent and trivalent ions calculated for L = 12;16;20 and several di erent tem peratures . Curve a, = 0:1; curve b, = 0:3; curve c, = 0:6; curve d, = 1. Inset: The average sam arium valence in the Sm $_1$ $_x$ M $_x$ B $_6$ system s (M = Y $^{3+}$;La $^{3+}$;Sr $^{2+}$;Yb $^{2+}$) m easured at 300 K (Ref. 14).

To determ ine the nite-size e ects all concentration dependences have been calculated for several cluster sizes (L = 12;16;20) and displayed on the comm on linear scale. We have found that for all exam ined temperatures the nite-size e ects are negligible (over the whole range of x plotted) and thus these results can be used satisfactorily to represent the behavior of macroscopic systems. It is seen that the substitution of rare-earth ions by trivalent and divalent ions produces fully di erent e ects. While in the 11st case the average occupancy of f-orbitals increases with increasing dopant concentration x, in the second case n_f decreases. In all exam ined cases the valence transition realizes continuously. Com paring these results with experim ental measurements of the average sam arium valence v (see inset in Fig. 1) in the Sm $_1$ $_x$ M $_x$ B $_6$ systems [14, 15] (M = Y $^{3+}$; La $^{3+}$; Sr $^{2+}$; Y b^{2+}) one can india good qualitative agreem ent between the theoretical and experim ental results. Indeed, the substitution of Sm by non-magnetic divalent ions (Sr^{2+} ; Yb^{2+}) increases the average sam arium valence (the average occupancy of f orbitals $n_{\rm f}$ = 3 v decreases), whereas the substitution of Sm by non-magnetic trivalent ions (Y 3+; La3+) produces the opposite e ect. These results again indicate that the FKM, in spite of its relative simplicity could, in principle, yield the correct physics for describing rare-earth com pounds. Even, also small quantitative deviations between the experimental and theoretical results can be straightforwardly improved within the FKM by optimizing the $n_f(x)$ behavior with respect to and E_f . This is illustrated in Fig. 2, where the xdependence of the f-orbital occupancy is plotted for = 1 (this relatively large value is chosen to ensure that is much greater than the spacing of many-body energylevels for both D = 1 and D = 2) and several dierent values of $E_{\rm f}$. It is seen that for nonzero values of E $_{\mathrm{f}}$ a nice correspondence between the theoretical and experim ental results can be achieved. Of course, one can take objection that realm aterials are three dim ensional, while our results have been obtained for the one dim ensional case. Unfortunately, due to limitations (mentioned above) on the size of clusters that can be treated exactly by sm all-cluster exact-diagonalization calculations (L = 20) we are not able to obtain any exact results in three dimensions. However, in two dim ensions there are several nite clusters with L = 10;16;18;20 that are accessible to exact-diagonalization calculations [18] and can be used to test the stability of obtained results with increasing dimension. The numerical calculations that we

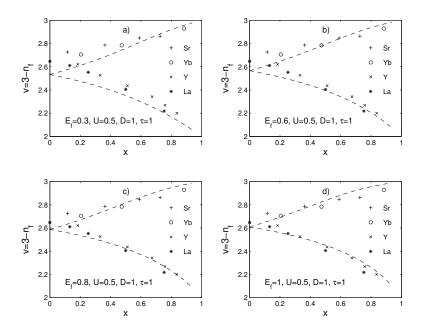


Figure 2: Comparison of the one-dimensional theoretical (dashed lines) and experimental results for the average Sm valence v=3 $n_{\rm f}$ as a function of x. The theoretical results have been calculated for U=0.5; = 1 and severaldierent values of the f-level position $E_{\rm f}$. The nite-size elects are negligible, on the linear scale it is not possible on the drawing to distinguish behaviors obtained for L=12;16 and 20 over the whole range of x plotted. The experimental results have been obtained for T=300 K.

have perform ed in two dimensions (for the same set of model parameters as in D=1 and the above mentioned cluster sizes) showed (see Fig. 3) that the f-occupancy of rare-earth orbitals depends only very weakly on the dimension of the system. Thus we can conclude that the spinless FKM, when treated exactly, can provide a reasonable theoretical description of valence transitions induced by doping in some rare-earth compounds, e.g., the sam arium hexaboride solid solutions Sm₁ $_{\rm x}$ M $_{\rm x}$ B $_{\rm 6}$ M = Y $^{3+}$; La $^{3+}$; S $^{2+}$; Y $^{2+}$). Of course, this statement can not be extended automatically on all them odynamics characteristics of the doped FKM. For example, to do quantitative comparison between the theoretical and experimental results for the special cheat and the magnetic susceptibility, the model should be rst generalized by including the spin and orbital dynamics that description was too simplified in the Hamiltonian (1). The work in this direction is currently in progress.

In sum mary, the extrapolation of small-cluster exact-diagonalization calculations

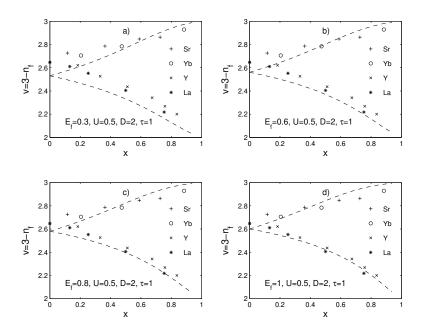


Figure 3: Comparison of the two-dimensional theoretical (dashed lines) and experimental results for the average Sm valence v=3 n_f as a function of x. The theoretical results have been obtained on clusters with L=10;16;20 for the same set of U; and E_f values as in D=1. Again, the nite-size e ects are negligible.

was used to study the in uence of doping on valence transitions in the spinless FKM at nonzero temperatures. Two types of doping were examined, and namely, the substitution of rare-earth ions by non-magnetic ions that introduce (i) one or (ii) none additional electron (per non-magnetic ion) into the conduction band. It was found that the rst type of substitution increases the average f-state occupancy of rare-earth ions, whereas the second type of substitution has the opposite elect. In all examined cases valence changes are continuous. The results obtained were used to describe valence transition behavior of samarium in the hexaboride solid solutions $Sm_1 \ _xM \ _xB_6 \ (M = Y^{3+}; La^{3+}; Sr^{2+}; Yb^{2+})$ and a very good agreement of theoretical and experimental results was found.

A cknow ledgm ents

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